



Synchrotron studies of nanocrystal thin film self-assembly

D. Pontoni,¹ K. J. Alvine,¹ A. Checco,³ O. Gang,⁴ B. Ocko,³ P. S. Pershan,^{1,2} & F. Stellacci.⁵

¹Division of Engineering and Applied Sciences and ²Department of Physics, Harvard University; ³Department of Physics and ⁴Center for Functional Nanomaterials, Brookhaven National Lab; ⁵Department of Materials Science and Engineering, MIT;

Motivation

Investigate fundamental aspects of nanocrystal self-assembly on solid substrates with particular attention to:

1. Intermediate thermodynamic equilibrium states rather than final products of irreversible non-equilibrium processes.
2. Effect of thin wetting solvent films on the assembly microstructure.
3. Nanocrystals with complex size distributions and stabilizing layers.
4. Influence of nanocrystal size and solvent quality.
5. In-situ determination of nanocrystal-substrate separation and in-plane nearest-neighbor distance.

Conventional investigative approach

- (a) Deposit a droplet of nanocrystal solution on substrate.
- (b) Let solvent evaporate.
- (c) Study final local microstructure by imaging techniques.



Our alternative approach

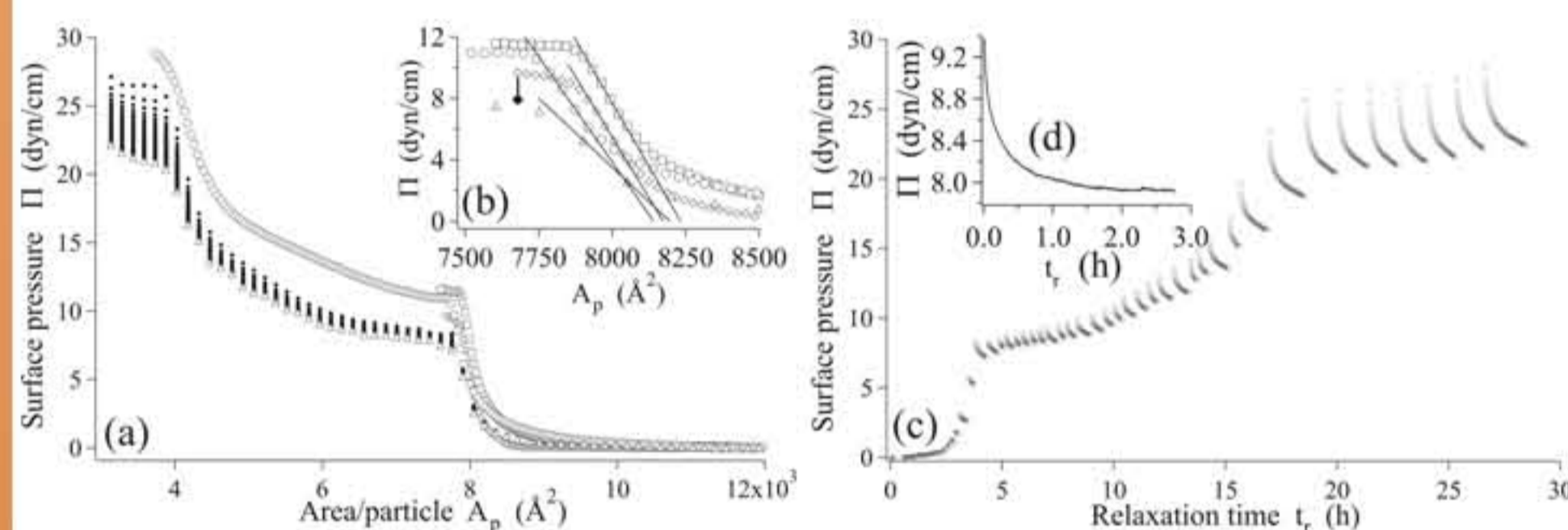
- (1) Prepare dry nanocrystal layers on substrates.
- (2) Generate stable nano-thin liquid wetting films.
- (3) Measure equilibrium microstructure in-situ by surface X-ray scattering.



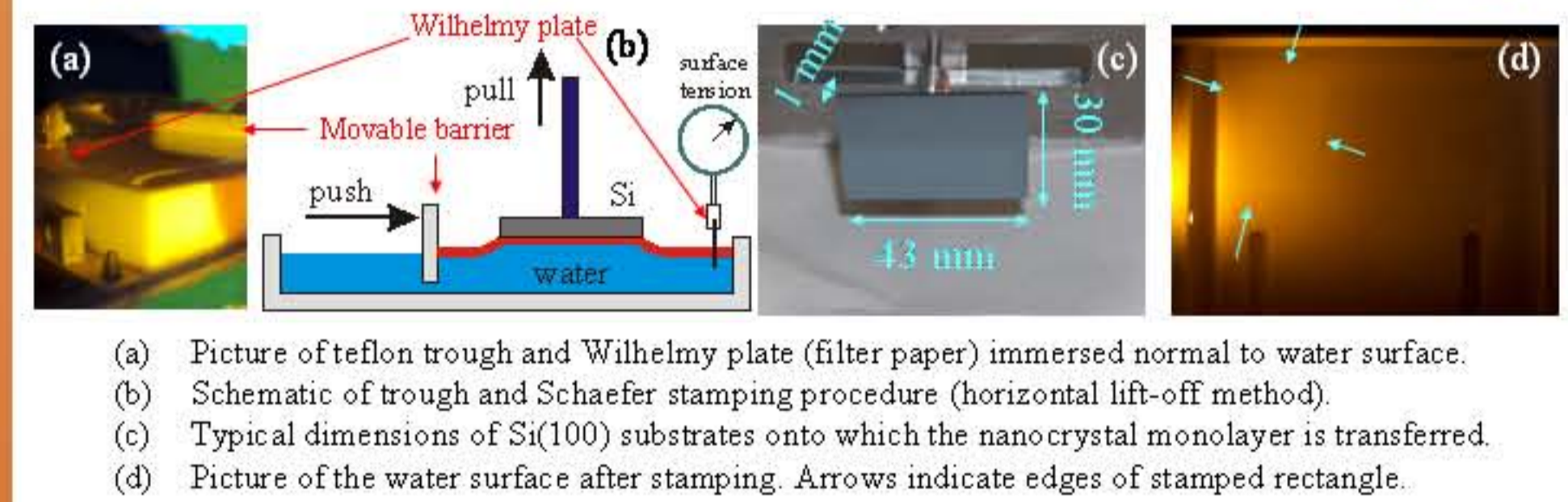
Typical particle size range: ~ 10-100 Å
Typical wetting film thickness range: ~ 1-100 Å

Methods

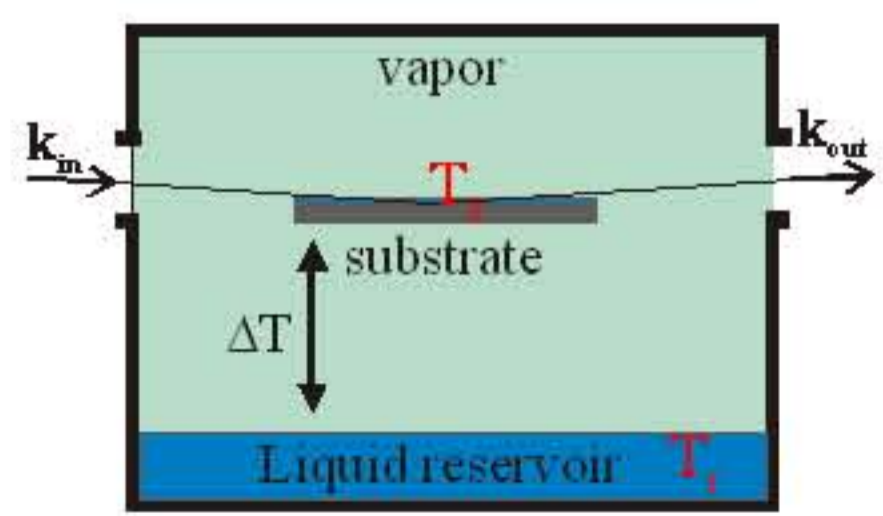
(1) Prepare nanocrystal monolayers on water: Langmuir isotherms



(2) Transfer monolayers to silicon substrates: Schaefer stamping



(3) Form stable liquid wetting films: controlled nano-wetting

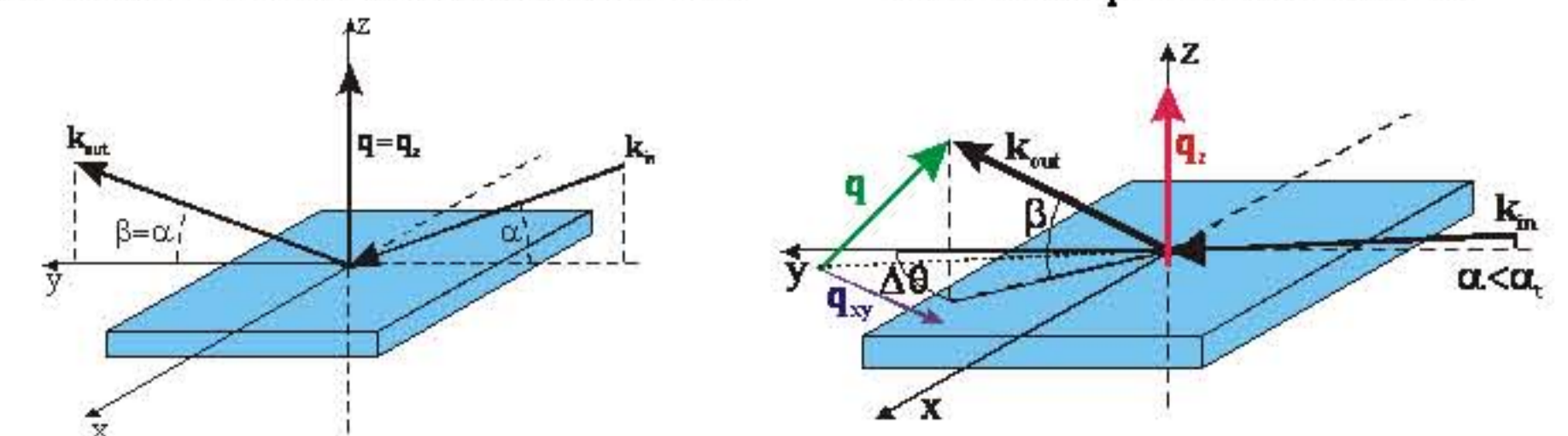


The thickness of the liquid film adsorbed on the substrate from vapor is controlled through the positive temperature offset ΔT .

$$\Delta T = T_s - T_r \geq 0$$

T_s : substrate temperature
 T_r : liquid reservoir (ambient) temperature
 $t \sim (\Delta T)^{-1/3}$: thickness of the adsorbed liquid layer

- (4) Measure average microstructure by surface X-ray scattering
X-ray reflectivity (XR) Measure microstructure normal to substrate
Grazing incidence diffraction (GID) Measure in-plane microstructure

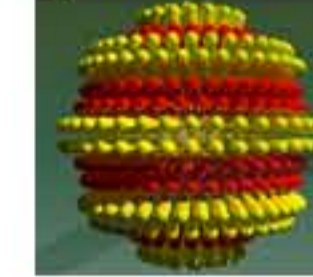


Results

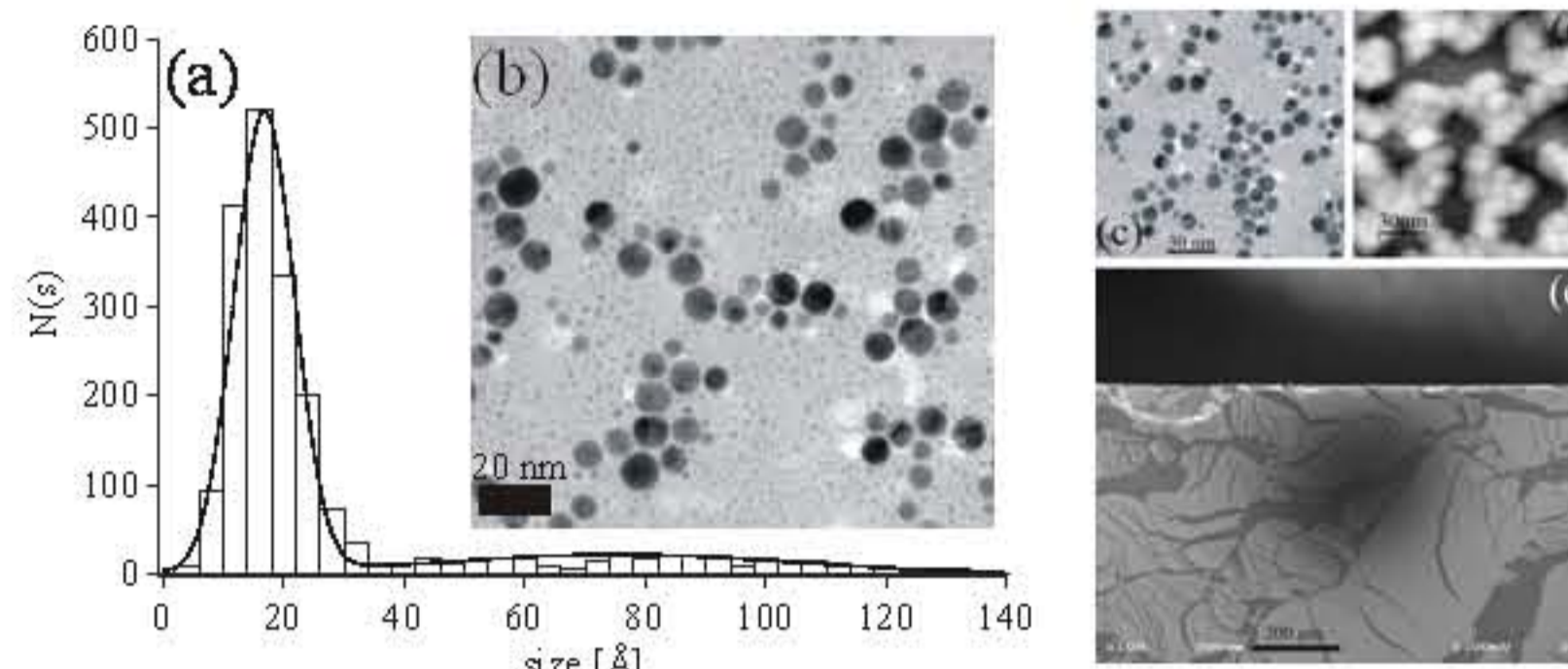
(A) Sample preparation and characterization.

(A1) Particles: bifunctional thiol-stabilized gold nanocrystals.

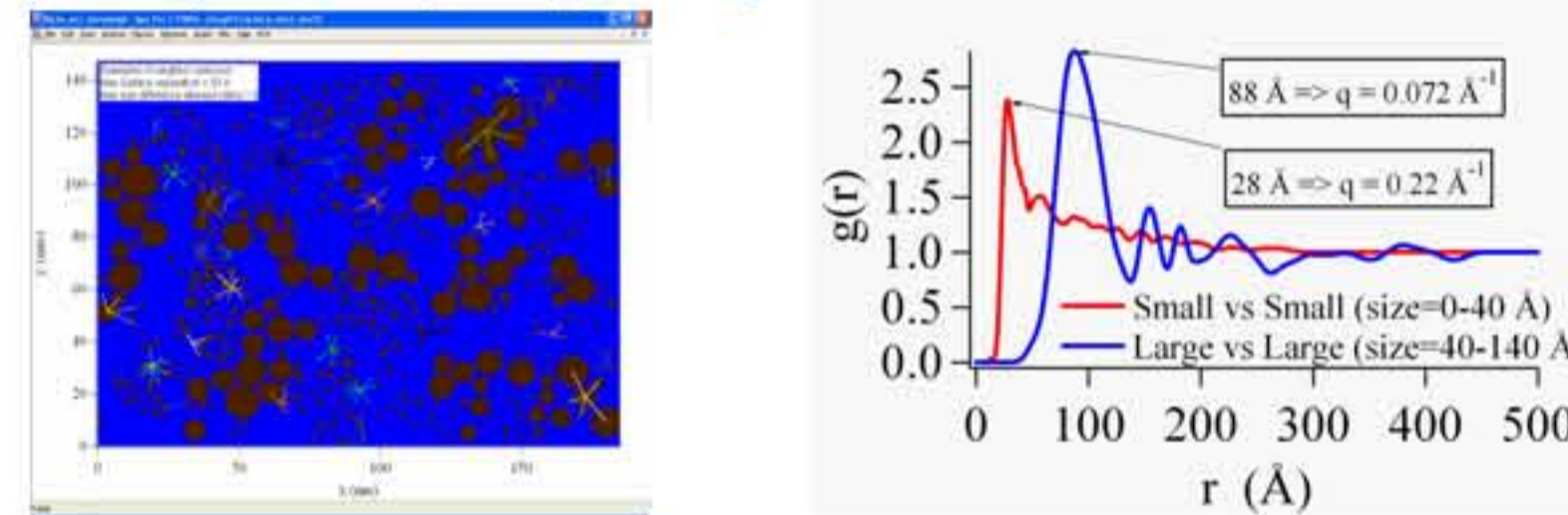
Stabilizing layer = 2:1 mixture of OT:MPA
OT = octanethiol = $\text{CH}_3-(\text{CH}_2)_7-\text{SH}$
MPA = mercaptopropionic acid = $\text{HOOC}-(\text{CH}_2)_2-\text{SH}$
Chain lengths: OT ~ 6 Å; MPA ~ 12 Å



(A2) Microscopy: nanocrystal size and monolayer stamping quality.

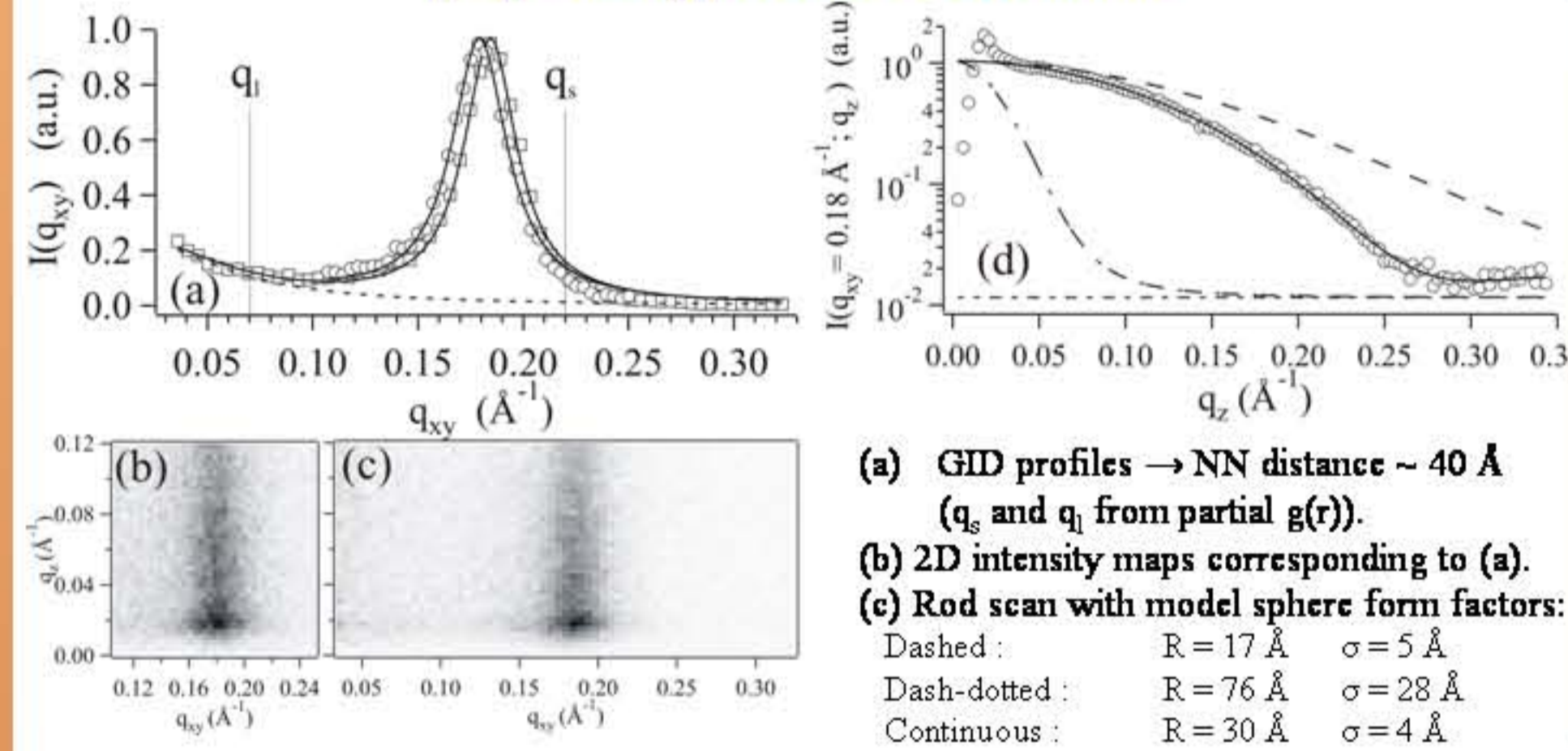


(A3) Real-space analysis: partial pair correlation functions.

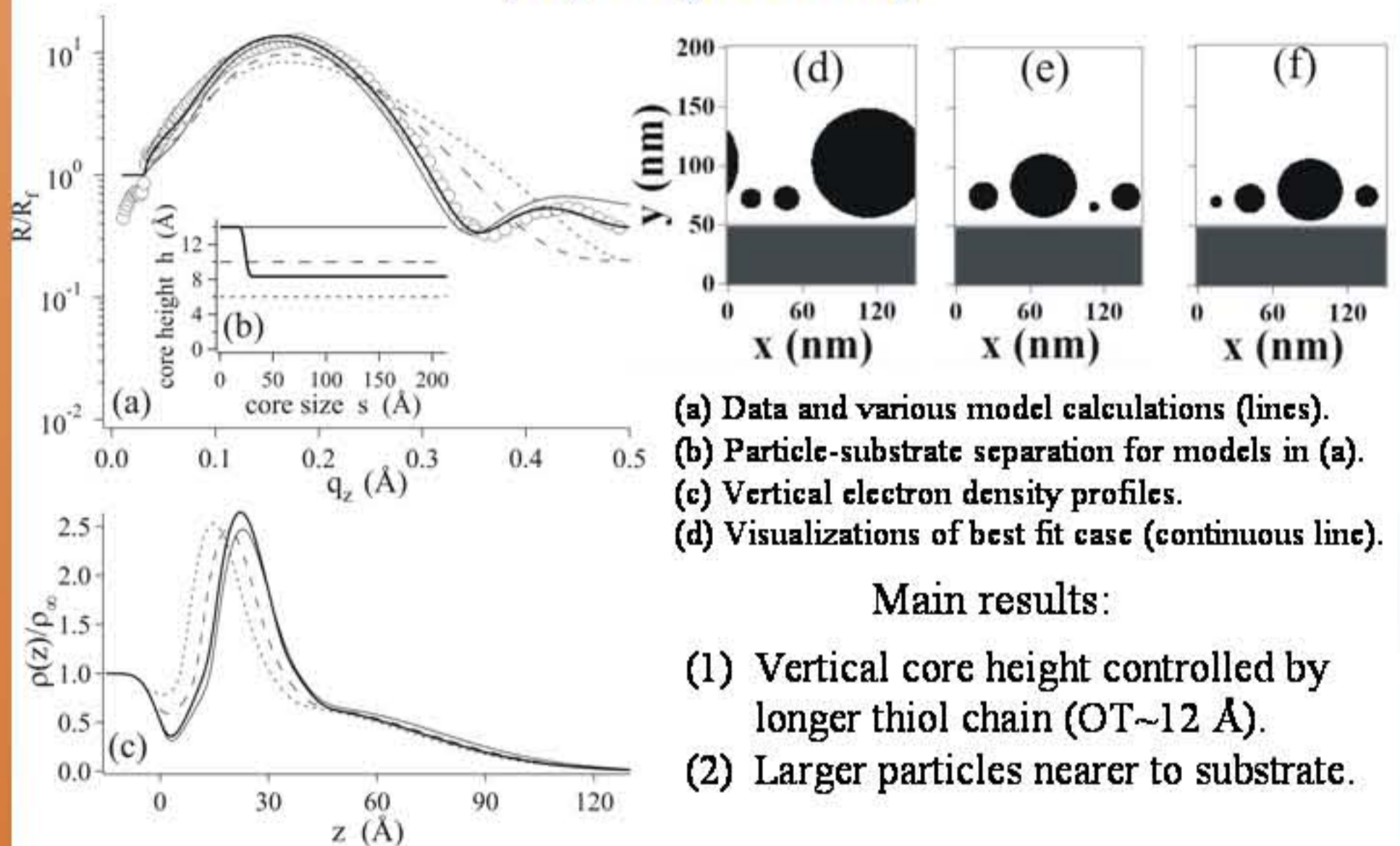


(B) Dry nanocrystal monolayers on silicon: X-ray results

(B1) Grazing Incidence Diffraction

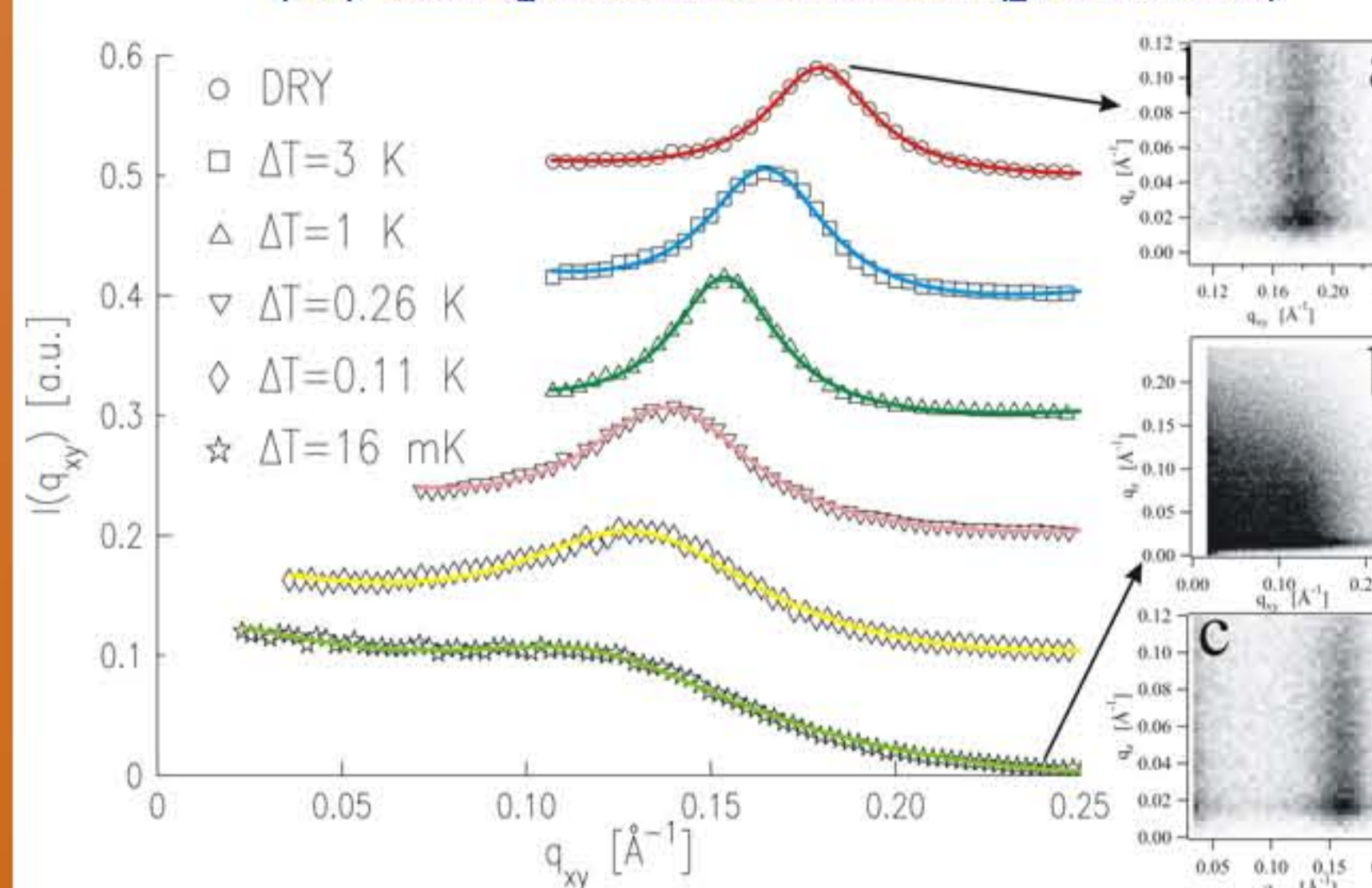


(B2) X-ray reflectivity



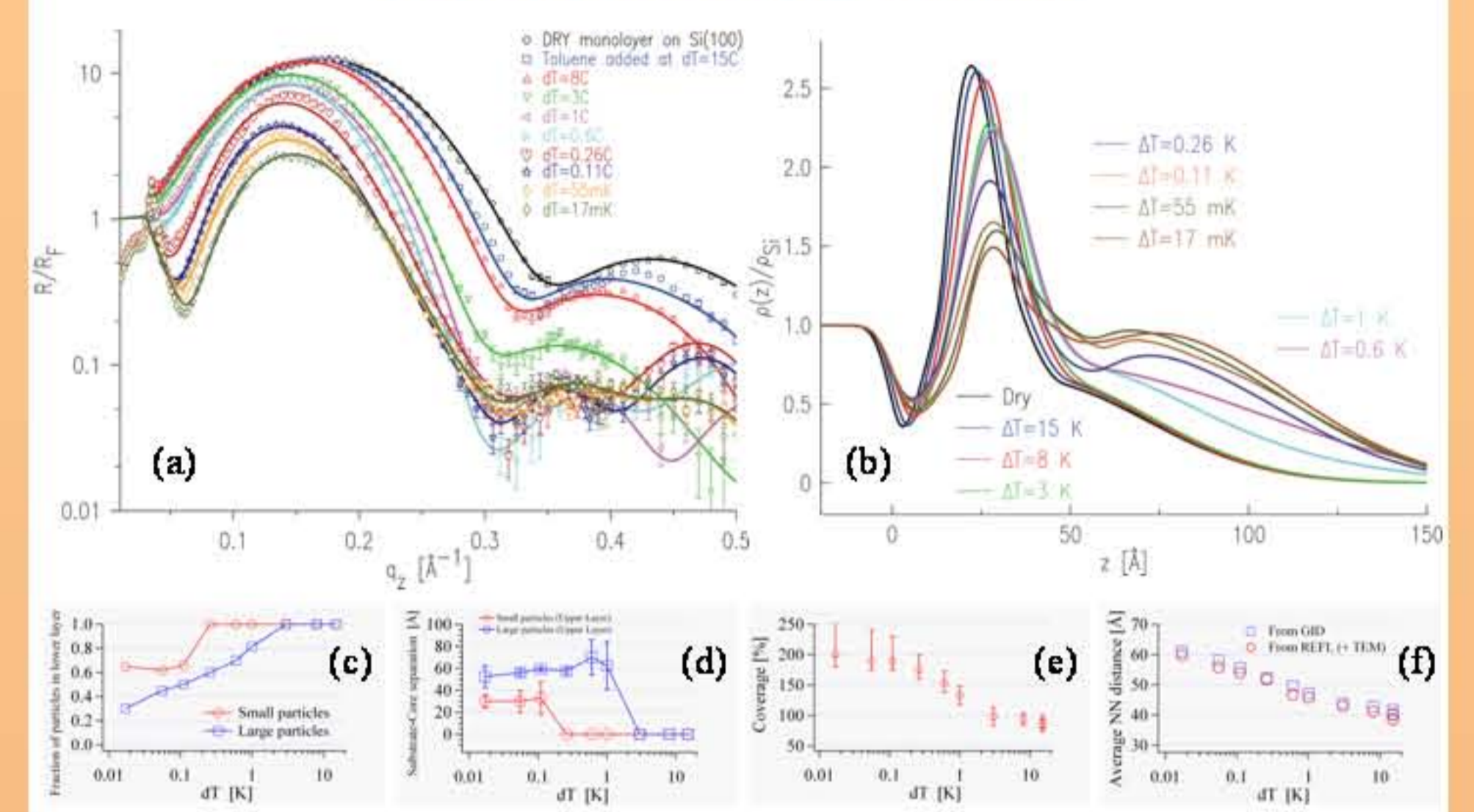
(C) Controlled nano-wetting with a good solvent (toluene)

(C1) Grazing incidence diffraction (good solvent)



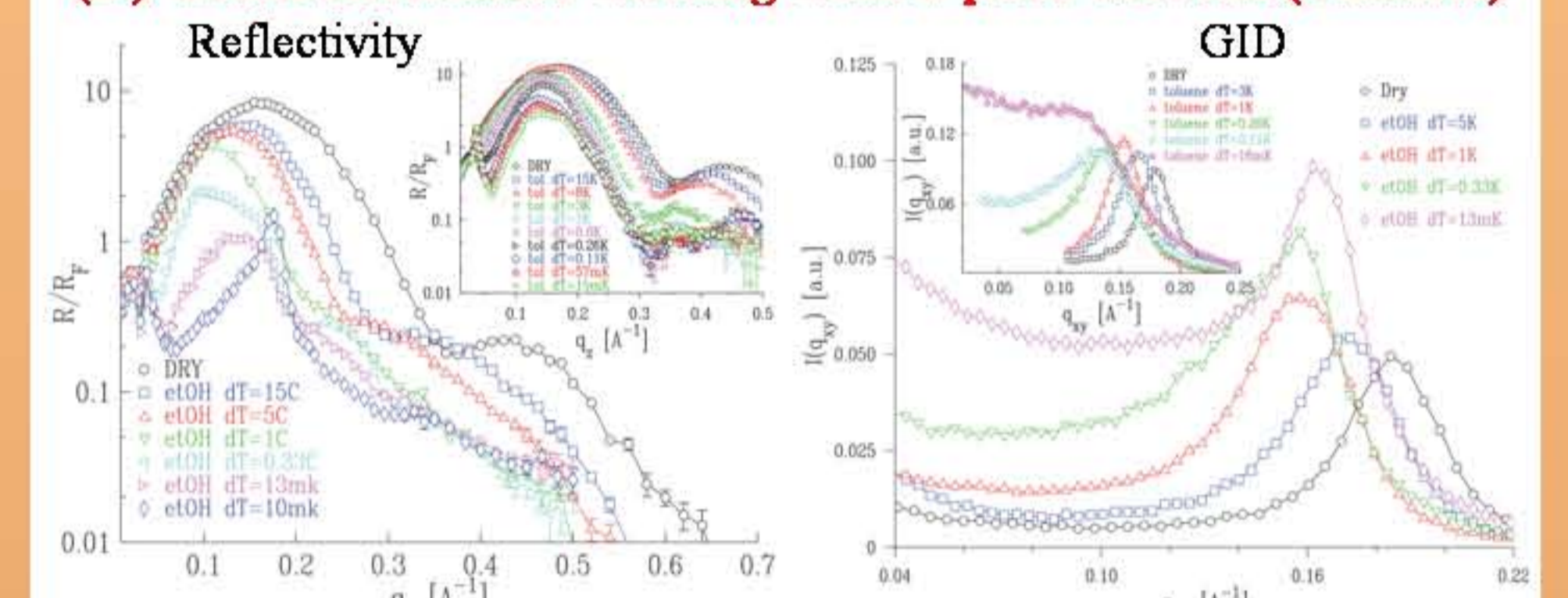
Thin wetting liquid (large ΔT) \rightarrow increasing NN distance, monolayer expansion.
Thick wetting liquid (small ΔT) \rightarrow increased disorder, dissolution.
Invert ΔT (back to large) \rightarrow monolayer re-assembly (panel (c)), reversible process, monolayer annealing.

(C2) X-ray reflectivity (good solvent)

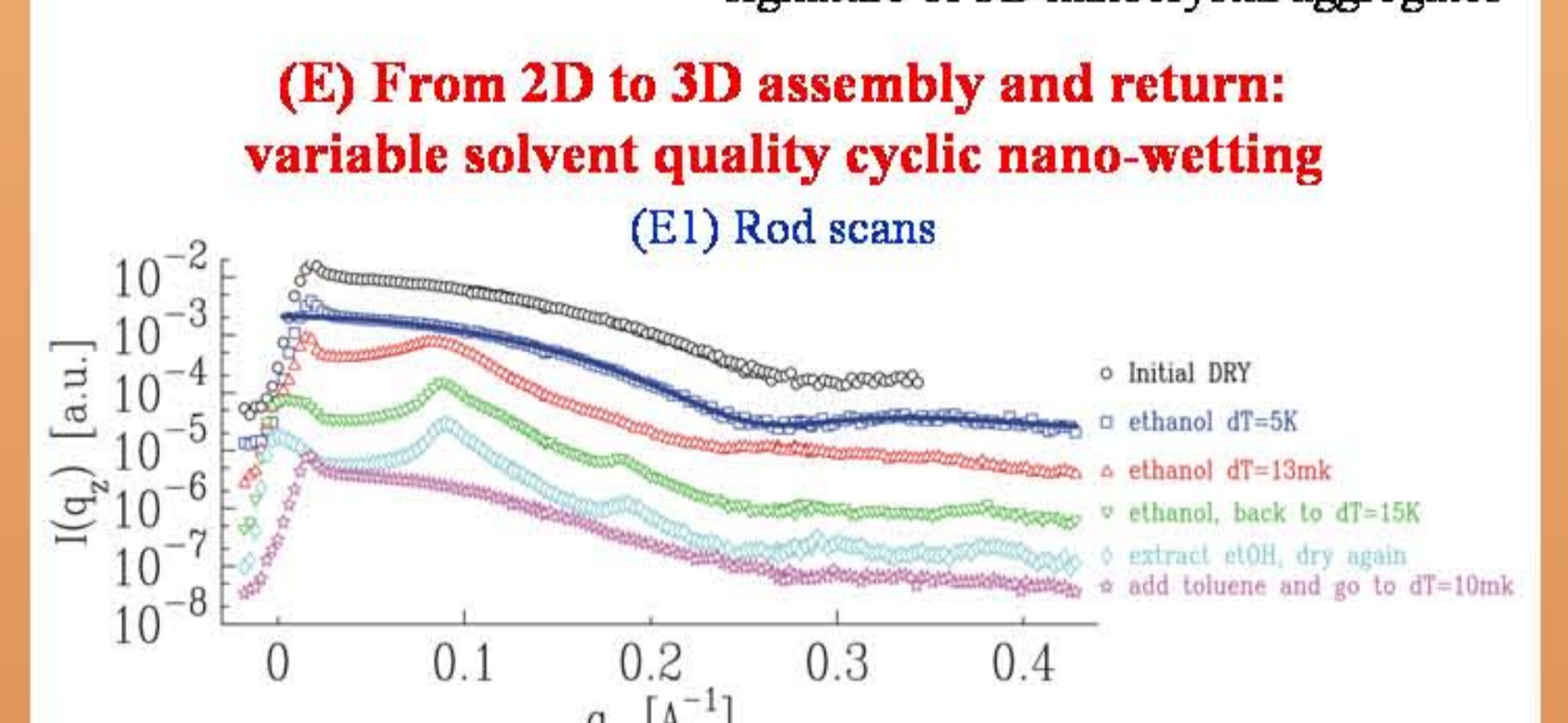


Main results
• Monolayer expansion up to ~100% coverage
• Further evolution resembles a bilayer transition
• Large particles are first promoted to upper layer

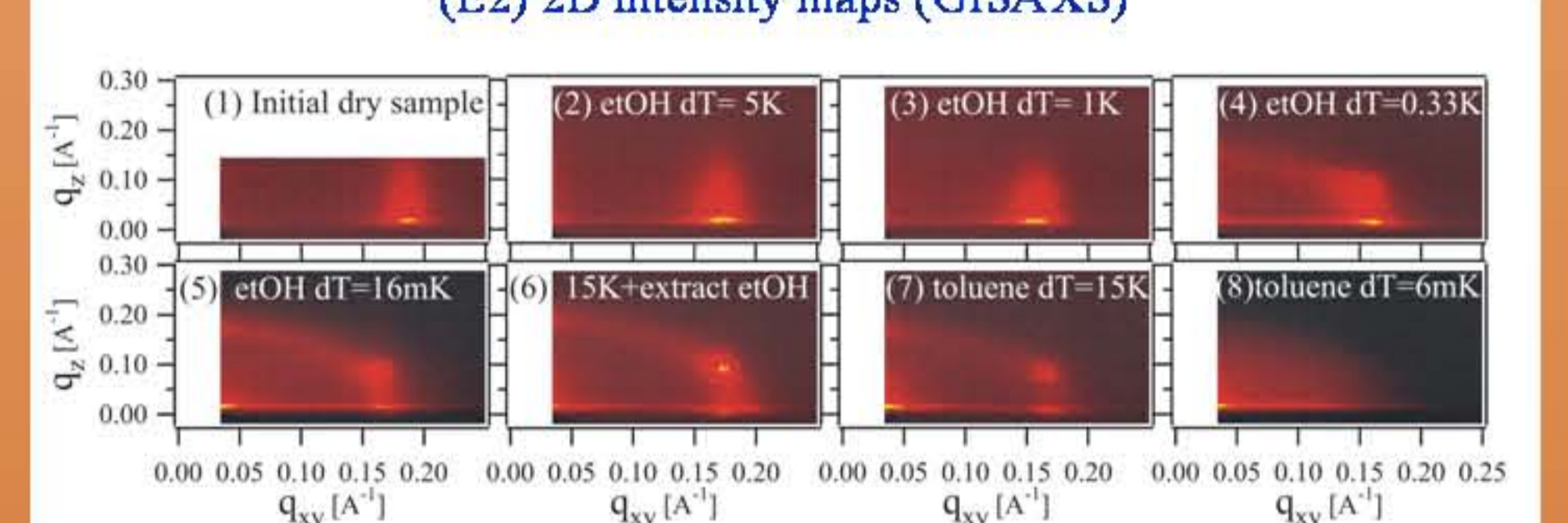
(D) Controlled nano-wetting with a poor solvent (ethanol)



(E) From 2D to 3D assembly and return: variable solvent quality cyclic nano-wetting

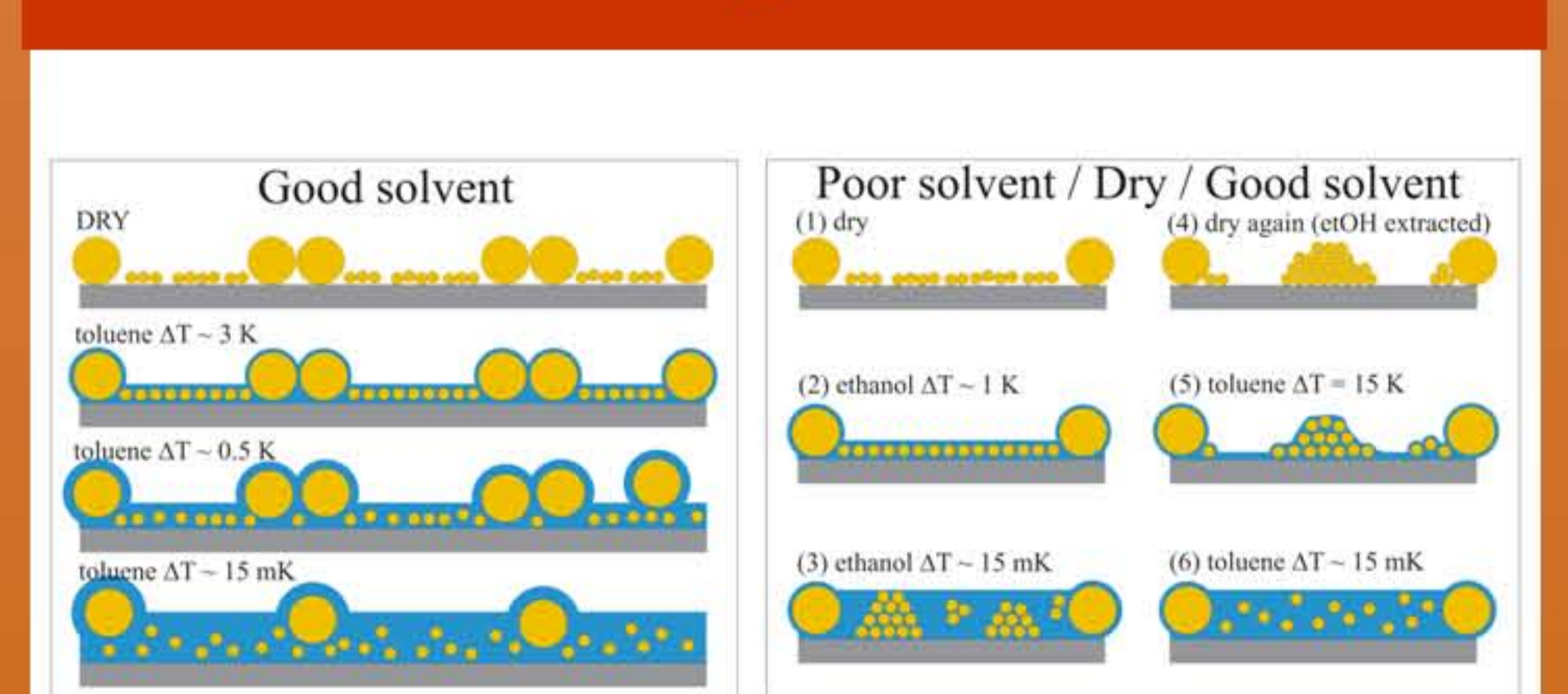


(E2) 2D intensity maps (GISAXS)



Main results
• Aggregates compacted and annealed by ethanol thinning and drying.
• Aggregates loosened by exchange to toluene and dissolved by toluene thickening.
• Initial monolayer can be re-assembled by final toluene thinning.

Pictorial Summary



Acknowledgements

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